

**EECS 277C Nanotechnology**  
**Homework #3 Solutions**

1) What is the Fermi wavelength of electrons in aluminum? Is it possible to fabricate 1d Al wires using photolithography? Is it possible to fabricate Al wires using electron beam lithography?

3.6 angstroms.

No.

2) Find the resistivity of pure copper at room temperature. Now, find the density of electrons in copper, assuming one free electron per atom. Now, calculate the scattering time and the mean free path of the electrons from the Drude model. Is it possible to fabricate copper wires in the ballistic limit using photolithography? Is it possible to fabricate copper wires in the ballistic limit using electron beam lithography?

$$10 \text{ microohm-cm} \quad 8.45 \cdot 10^{22} \text{ cm}^{-3} \quad \frac{1}{\rho} = \sigma = \frac{ne^2\tau}{m}$$

$$\tau = 4 \cdot 10^{-15} \text{ s} \quad l = v_{\text{Fermi}}\tau$$

$$v_{\text{Fermi}} = 1.6 \times 10^8 \text{ cm/s} \quad \text{so } l = 6.4 \text{ nm}$$

No

No

3) For a 2DEG in GaAs with  $n=10^{11} \text{ cm}^{-2}$  and a mobility of 8,000  $\text{cm}^2/\text{V-s}$  (typical of room temperature HEMT operation), calculate the scattering time and the mean free path from the Drude model. Is it possible to fabricate devices using lithography that are smaller than the mean free path? Remember you must use the effective mass of electrons for the Fermi energy, etc.

$$\mu = \frac{e\tau}{m^*} \quad \tau = 0.3 \text{ ps} \quad l = v_{\text{Fermi}}\tau \quad \text{so } l = 1.3 \cdot 10^5 \text{ m/s} \times 0.3 \text{ ps} = 40 \text{ nm}$$

Yes